

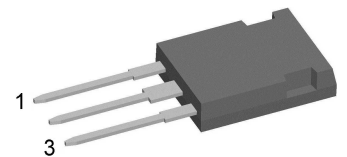
Schottky Diode

$$\begin{aligned} V_{RRM} &= 150 \text{ V} \\ I_{FAV} &= 2 \times 30 \text{ A} \\ V_F &= 0,66 \text{ V} \end{aligned}$$

High Performance Schottky Diode
 Low Loss and Soft Recovery
 Common Cathode

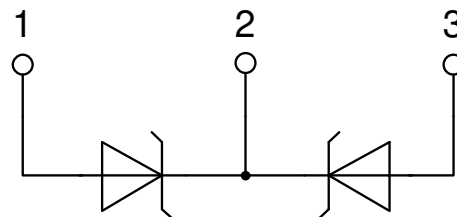
Part number

DSSK60-015AR



Backside: isolated

 E72873



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: ISOPLUS247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

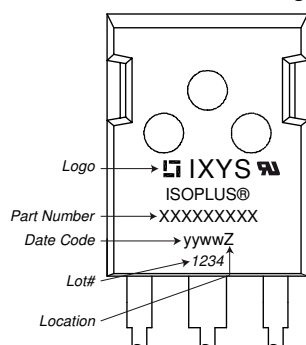
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Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				150	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				150	V
I_R	reverse current, drain current	$V_R = 150\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2	mA
		$V_R = 150\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			5	mA
V_F	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			0,81	V
		$I_F = 60\text{ A}$				0,93	V
		$I_F = 30\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0,66	V
		$I_F = 60\text{ A}$				0,80	V
I_{FAV}	average forward current	$T_C = 115^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			30	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0,43	V
r_F	slope resistance					4,8	mΩ
R_{thJC}	thermal resistance junction to case					0,8	K/W
R_{thCH}	thermal resistance case to heatsink				0,25		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				190	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			600	A
C_J	junction capacitance	$V_R = 24\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		481		pF
E_{AS}	non-repetitive avalanche energy	$I_{AS} = 4\text{ A}$ $L = 100\text{ }\mu\text{H}$	$T_{VJ} = 25^{\circ}\text{C}$			0,8	mJ
I_{AR}	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ. $f = 10\text{ kHz}$				0,4	A

Package ISOPLUS247				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ⁿ				70	A
T_{VJ}	virtual junction temperature			-55		175	°C
T_{op}	operation temperature			-55		150	°C
T_{stg}	storage temperature			-55		150	°C
Weight					6		g
F_c	mounting force with clip			20		120	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal		2,7			mm
$d_{Spb/Apb}$		terminal to backside		4,1			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600			V
		t = 1 minute		3000			V

Product Marking



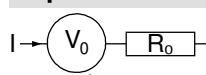
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSSK60-015AR	DSSK60-015AR	Tube	30	501661

Similar Part	Package	Voltage class
DSSK60-015A	TO-247AD (3)	150

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



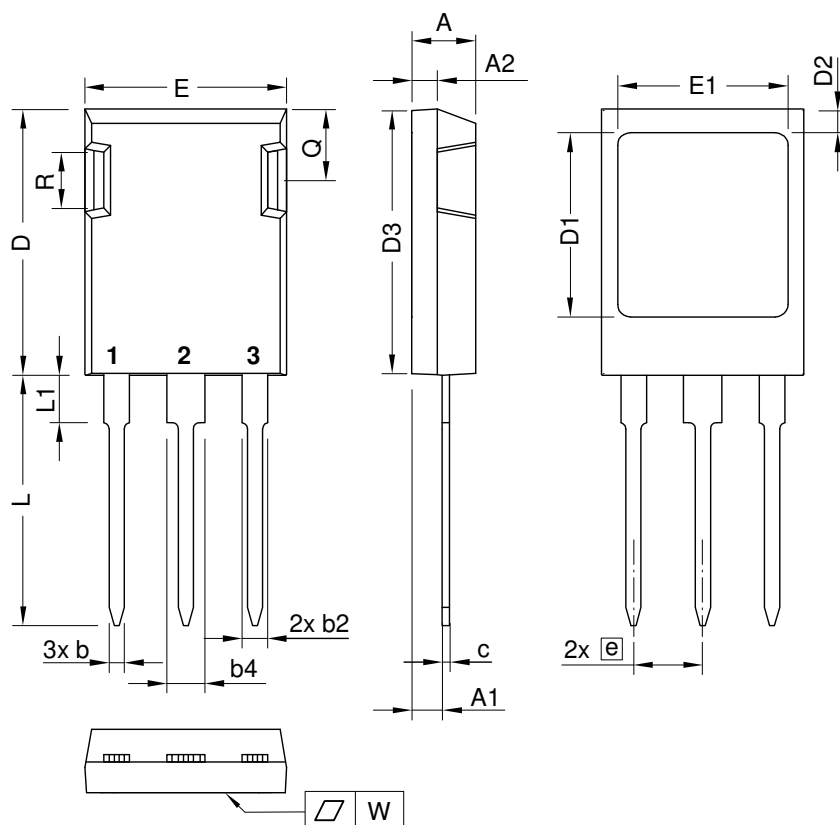
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$V_{0\max}$ threshold voltage 0,43

V

$R_{0\max}$ slope resistance * 1,7

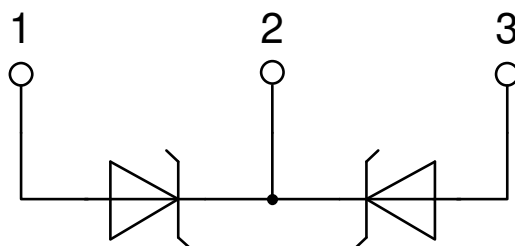
mΩ

Outlines ISOPLUS247


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b2	1.91	2.20	0.075	0.087
b4	2.92	3.24	0.115	0.128
c	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
D1	15.75	16.26	0.620	0.640
D2	1.65	2.15	0.065	0.085
D3	20.30	20.70	0.799	0.815
E	15.75	16.13	0.620	0.635
E1	13.21	13.72	0.520	0.540
e	5.45 BSC		0.215 BSC	
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
Q	5.59	6.20	0.220	0.244
R	4.25	5.50	0.167	0.217
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und L_{max} .
 This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except L_{max} .



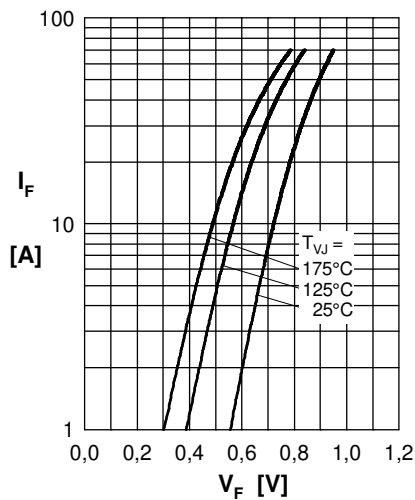
Schottky


Fig. 1 Max. forward voltage drop characteristics

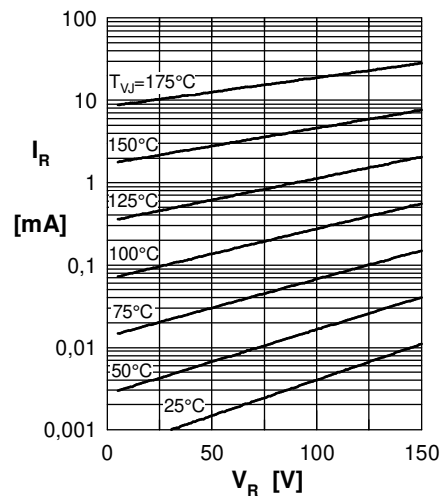
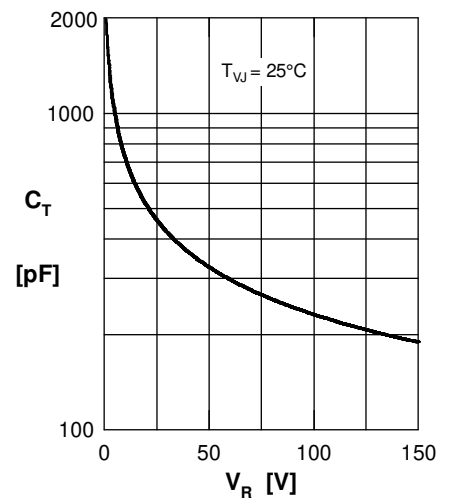
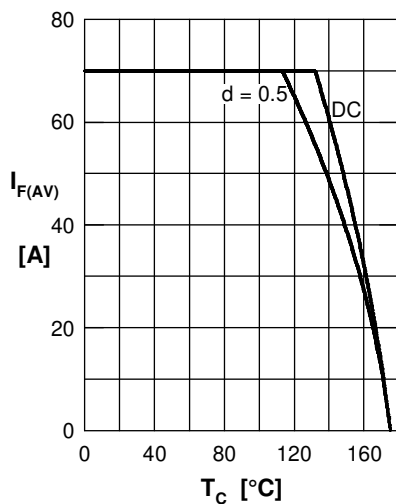
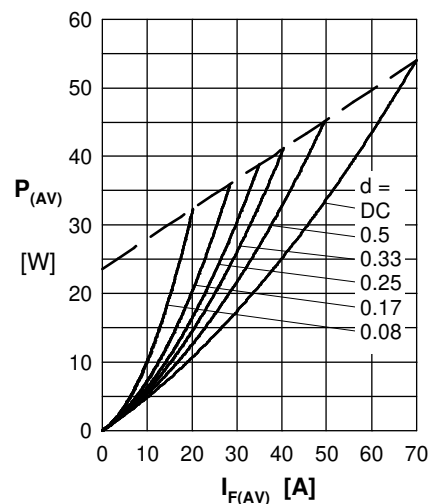

 Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

 Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

 Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp. T_C


Fig. 5 Forward power loss characteristics

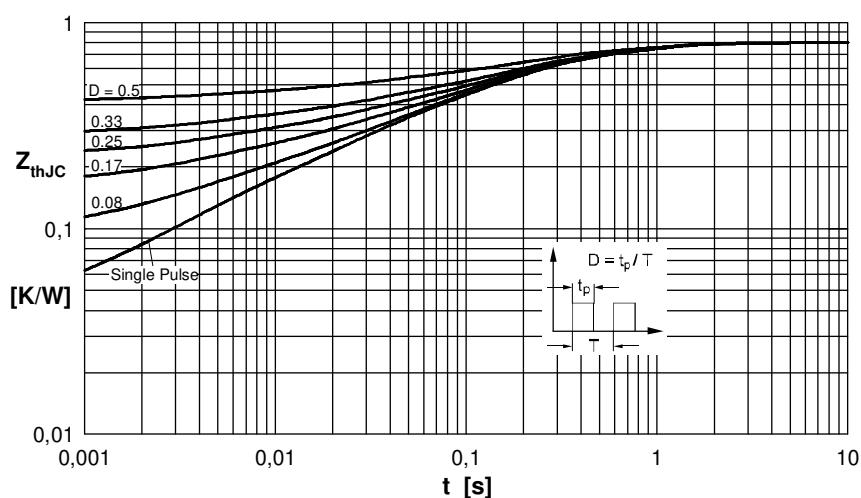


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode